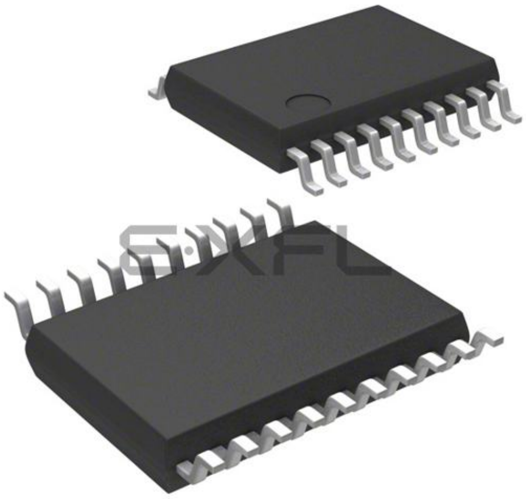

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	15
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 12x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f031f6p6tr

In Standby mode, it is put in power down mode. In this mode, the regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption (but the contents of the registers and SRAM are lost).

3.5.4 Low-power modes

The STM32F031x4/x6 microcontrollers support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.
- **Stop mode**

  Stop mode achieves very low power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low power mode.

  The device can be woken up from Stop mode by any of the EXTI lines. The EXTI line source can be one of the 16 external lines, the PVD output, RTC, I2C1 or USART1.

  USART1 and I2C1 peripherals can be configured to enable the HSI RC oscillator so as to get clock for processing incoming data. If this is used when the voltage regulator is put in low power mode, the regulator is first switched to normal mode before the clock is provided to the given peripheral.
- **Standby mode**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the RTC domain and Standby circuitry.

  The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pins, or an RTC event occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped by entering Stop or Standby mode.

3.6 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-32 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example on failure of an indirectly used external crystal, resonator or oscillator).

Several prescalers allow the application to configure the frequency of the AHB and the APB domains. The maximum frequency of the AHB and the APB domains is 48 MHz.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

3.10.1 Temperature sensor

The temperature sensor (TS) generates a voltage V_{SENSE} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC_IN16 input channel which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Table 3. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at a temperature of 30 °C (± 5 °C), V_{DDA}= 3.3 V (± 10 mV)	0x1FFF F7B8 - 0x1FFF F7B9
TS_CAL2	TS ADC raw data acquired at a temperature of 110 °C (± 5 °C), V_{DDA}= 3.3 V (± 10 mV)	0x1FFF F7C2 - 0x1FFF F7C3

3.10.2 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC. V_{REFINT} is internally connected to the ADC_IN17 input channel. The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 4. Internal voltage reference calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at a temperature of 30 °C (± 5 °C), V_{DDA}= 3.3 V (± 10 mV)	0x1FFF F7BA - 0x1FFF F7BB

3.10.3 V_{BAT} battery voltage monitoring

This embedded hardware feature allows the application to measure the V_{BAT} battery voltage using the internal ADC channel ADC_IN18. As the V_{BAT} voltage may be higher than V_{DDA}, and thus outside the ADC input range, the V_{BAT} pin is internally connected to a bridge divider by 2. As a consequence, the converted digital value is half the V_{BAT} voltage.

3.16 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

Table 10. Legend/abbreviations used in the pinout table

Name		Abbreviation	Definition
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type		S	Supply pin
		I	Input-only pin
		I/O	Input / output pin
I/O structure		FT	5 V-tolerant I/O
		FTf	5 V-tolerant I/O, FM+ capable
		TTa	3.3 V-tolerant I/O directly connected to ADC
		TC	Standard 3.3V I/O
		B	Dedicated BOOT0 pin
		RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes		Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers	
	Additional functions	Functions directly selected/enabled through peripheral registers	

Table 11. Pin definitions

Pin number						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP48	LQFP32	UFQFPN32	UFQFPN28	WLCSP25	TSSOP20					Alternate functions	Additional functions
1	-	-	-	-	-	VBAT	S	-	-	Backup power supply	
2	-	-	-	-	-	PC13	I/O	TC	(1)(2)	-	RTC_TAMP1, RTC_TS, RTC_OUT, WKUP2
3	-	-	-	-	-	PC14-OSC32_IN (PC14)	I/O	TC	(1)(2)	-	OSC32_IN
4	-	-	-	-	-	PC15-OSC32_OUT (PC15)	I/O	TC	(1)(2)	-	OSC32_OUT
5	2	2	2	A5	2	PF0-OSC_IN (PF0)	I/O	FT	-	-	OSC_IN

Table 11. Pin definitions (continued)

Pin number						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP48	LQFP32	UFQFPN32	UFQFPN28	WLCSP25	TSSOP20					Alternate functions	Additional functions
30	19	19	19	C1	17	PA9	I/O	FTf	-	USART1_TX, TIM1_CH2, I2C1_SCL	-
31	20	20	20	B1	18	PA10	I/O	FTf	-	USART1_RX, TIM1_CH3, TIM17_BKIN, I2C1_SDA	-
32	21	21	-	-	-	PA11	I/O	FT	-	USART1_CTS, TIM1_CH4, EVENTOUT	-
33	22	22	-	-	-	PA12	I/O	FT	-	USART1_RTS, TIM1_ETR, EVENTOUT	-
34	23	23	21	A1	19	PA13 (SWDIO)	I/O	FT	(5)	IR_OUT, SWDIO	-
35	-	-	-	-	-	PF6	I/O	FTf	-	I2C1_SCL	-
36	-	-	-	-	-	PF7	I/O	FTf	-	I2C1_SDA	-
37	24	24	22	A2	20	PA14 (SWCLK)	I/O	FT	(5)	USART1_TX, SWCLK	-
38	25	25	23	-	-	PA15	I/O	FT	(6)	SPI1_NSS, I2S1_WS, TIM2_CH_ETR, EVENTOUT, USART1_RX	-
39	26	26	24	-	-	PB3	I/O	FT	(6)	SPI1_SCK, I2S1_CK, TIM2_CH2, EVENTOUT	-
40	27	27	25	-	-	PB4	I/O	FT	(6)	SPI1_MISO, I2S1_MCK, TIM3_CH1, EVENTOUT	-

Table 13. Alternate functions selected through GPIOB_AFR registers for port B

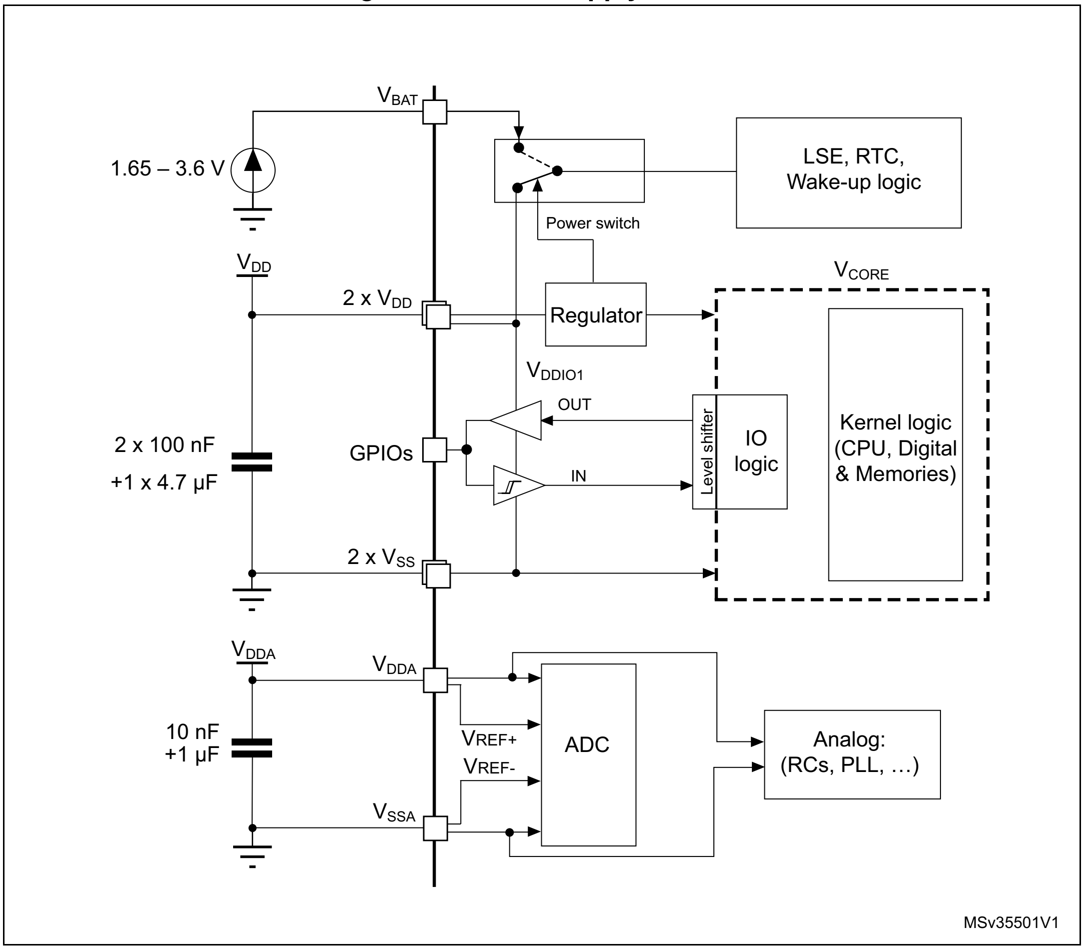
Pin name	AF0	AF1	AF2	AF3
PB0	EVENTOUT	TIM3_CH3	TIM1_CH2N	-
PB1	TIM14_CH1	TIM3_CH4	TIM1_CH3N	-
PB2	-	-	-	-
PB3	SPI1_SCK, I2S1_CK	EVENTOUT	TIM2_CH2	-
PB4	SPI1_MISO, I2S1_MCK	TIM3_CH1	EVENTOUT	-
PB5	SPI1_MOSI, I2S1_SD	TIM3_CH2	TIM16_BKIN	I2C1_SMBA
PB6	USART1_TX	I2C1_SCL	TIM16_CH1N	-
PB7	USART1_RX	I2C1_SDA	TIM17_CH1N	-
PB8	-	I2C1_SCL	TIM16_CH1	-
PB9	IR_OUT	I2C1_SDA	TIM17_CH1	EVENTOUT
PB10	-	I2C1_SCL	TIM2_CH3	-
PB11	EVENTOUT	I2C1_SDA	TIM2_CH4	-
PB12	SPI1_NSS	EVENTOUT	TIM1_BKIN	-
PB13	SPI1_SCK	-	TIM1_CH1N	-
PB14	SPI1_MISO	-	TIM1_CH2N	-
PB15	SPI1_MOSI	-	TIM1_CH3N	-

Table 14. STM32F031x4/x6 peripheral register boundary addresses (continued)

Bus	Boundary address	Size	Peripheral
APB	0x4000 7400 - 0x4000 7FFF	3KB	Reserved
	0x4000 7000 - 0x4000 73FF	1KB	PWR
	0x4000 5800 - 0x4000 6FFF	6KB	Reserved
	0x4000 5400 - 0x4000 57FF	1KB	I2C1
	0x4000 3400 - 0x4000 53FF	8KB	Reserved
	0x4000 3000 - 0x4000 33FF	1KB	IWDG
	0x4000 2C00 - 0x4000 2FFF	1KB	WWDG
	0x4000 2800 - 0x4000 2BFF	1KB	RTC
	0x4000 2400 - 0x4000 27FF	1KB	Reserved
	0x4000 2000 - 0x4000 23FF	1KB	TIM14
	0x4000 0800 - 0x4000 1FFF	6KB	Reserved
	0x4000 0400 - 0x4000 07FF	1KB	TIM3
	0x4000 0000 - 0x4000 03FF	1KB	TIM2

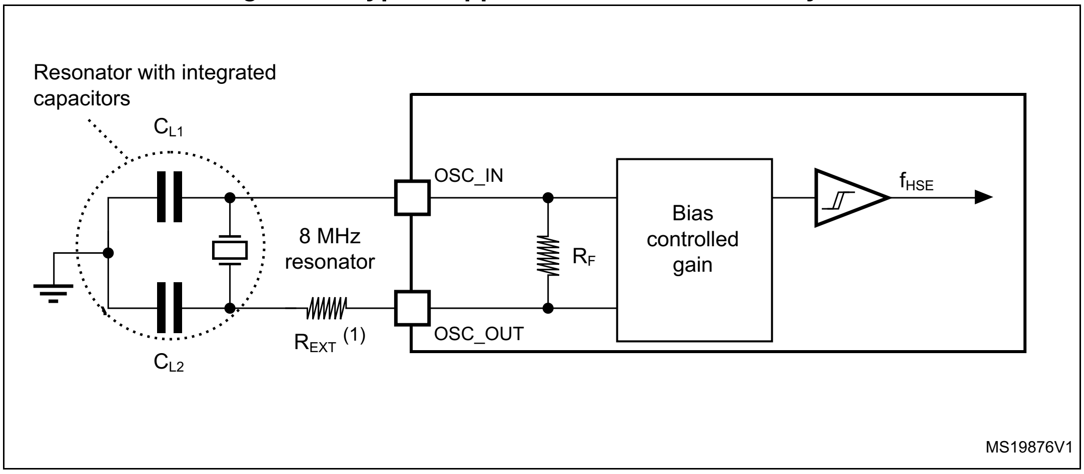
6.1.6 Power supply scheme

Figure 12. Power supply scheme



Caution: Each power supply pair (V_{DD}/V_{SS}, V_{DDA}/V_{SSA} etc.) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

Figure 16. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 34*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 34. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)

Symbol	Parameter	Conditions(1)	Min(2)	Typ	Max(2)	Unit
I_{DD}	LSE current consumption	low drive capability	-	0.5	0.9	µA
		medium-low drive capability	-	-	1	
		medium-high drive capability	-	-	1.3	
		high drive capability	-	-	1.6	
g_m	Oscillator transconductance	low drive capability	5	-	-	µA/V
		medium-low drive capability	8	-	-	
		medium-high drive capability	15	-	-	
		high drive capability	25	-	-	
$t_{SU(LSE)}$(3)	Startup time	V_{DDIOx} is stabilized	-	2	-	s

1. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.
2. Guaranteed by design, not tested in production.
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

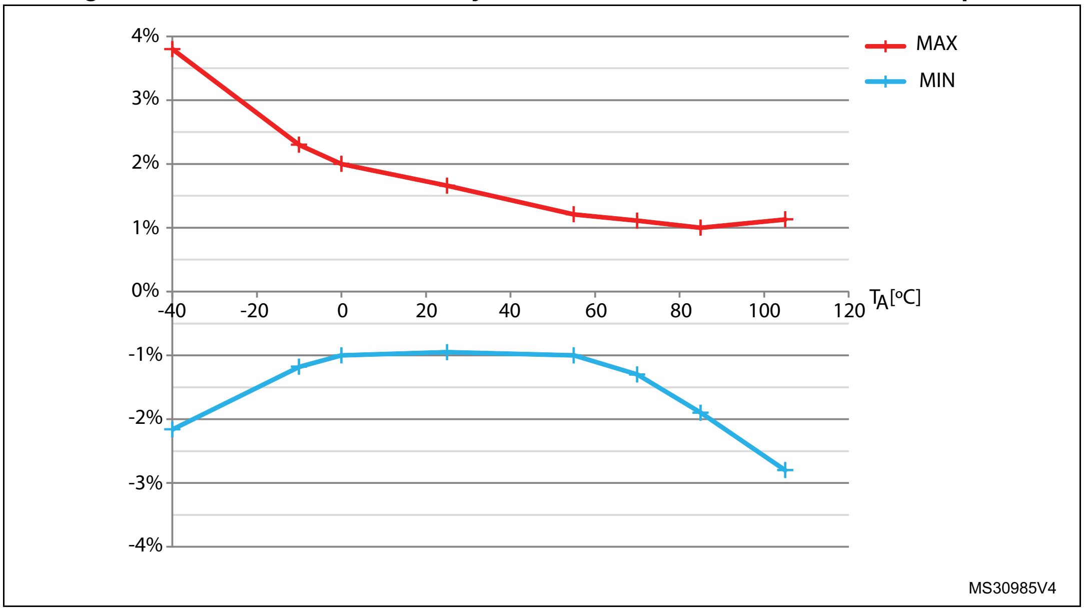
High-speed internal (HSI) RC oscillator

Table 35. HSI oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	8	-	MHz
TRIM	HSI user trimming step	-	-	-	1(2)	%
$DuCy_{(HSI)}$	Duty cycle	-	45(2)	-	55(2)	%
ACC_{HSI}	Accuracy of the HSI oscillator	T_A = -40 to 105°C	-2.8(3)	-	3.8(3)	%
		T_A = -10 to 85°C	-1.9(3)	-	2.3(3)	
		T_A = 0 to 85°C	-1.9(3)	-	2(3)	
		T_A = 0 to 70°C	-1.3(3)	-	2(3)	
		T_A = 0 to 55°C	-1(3)	-	2(3)	
		T_A = 25°C(4)	-1	-	1	
$t_{su(HSI)}$	HSI oscillator startup time	-	1(2)	-	2(2)	µs
$I_{DDA(HSI)}$	HSI oscillator power consumption	-	-	80	100(2)	µA

1. V_{DDA} = 3.3 V, T_A = -40 to 105°C unless otherwise specified.
2. Guaranteed by design, not tested in production.
3. Data based on characterization results, not tested in production.
4. Factory calibrated, parts not soldered.

Figure 18. HSI oscillator accuracy characterization results for soldered parts



Low-speed internal (LSI) RC oscillator

Table 37. LSI oscillator characteristics(1)

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}	Frequency	30	40	50	kHz
$t_{su(LSI)}$(2)	LSI oscillator startup time	-	-	85	µs
$I_{DDA(LSI)}$(2)	LSI oscillator power consumption	-	0.75	1.2	µA

1. V_{DDA} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design, not tested in production.

6.3.9 PLL characteristics

The parameters given in *Table 38* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 18: General operating conditions*.

Table 38. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max	
f_{PLL_IN}	PLL input clock(1)	1(2)	8.0	24(2)	MHz
	PLL input clock duty cycle	40(2)	-	60(2)	%
f_{PLL_OUT}	PLL multiplier output clock	16(2)	-	48	MHz
t_{LOCK}	PLL lock time	-	-	200(2)	µs
$Jitter_{PLL}$	Cycle-to-cycle jitter	-	-	300(2)	ps

1. Take care to use the appropriate multiplier factors to obtain PLL input clock values compatible with the range defined by f_{PLL_OUT}.
2. Guaranteed by design, not tested in production.

6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Table 39. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
t_{prog}	16-bit programming time	T_A = - 40 to +105 °C	40	53.5	60	µs
t_{ERASE}	Page (1 KB) erase time	T_A = - 40 to +105 °C	20	-	40	ms
t_{ME}	Mass erase time	T_A = - 40 to +105 °C	20	-	40	ms
I_{DD}	Supply current	Write mode	-	-	10	mA
		Erase mode	-	-	12	mA

1. Guaranteed by design, not tested in production.

Table 40. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min[(1)]	Unit
N_{END}	Endurance	T_A = –40 to +105 °C	10	kcycle
t_{RET}	Data retention	1 kcycle[(2)] at T_A = 85 °C	30	Year
		1 kcycle[(2)] at T_A = 105 °C	10	
		10 kcycle[(2)] at T_A = 55 °C	20	

1. Data based on characterization results, not tested in production.
2. Cycling performed over the whole temperature range.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 41*. They are based on the EMS levels and classes defined in application note AN1709.

Table 41. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP48, T_A = +25 °C, f_{HCLK} = 48 MHz, conforming to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP48, T_A = +25°C, f_{HCLK} = 48 MHz, conforming to IEC 61000-4-4	4B

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Table 46. I/O static characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor (3)	$V_{IN} = V_{SS}$	25	40	55	kΩ
R_{PD}	Weak pull-down equivalent resistor(3)	$V_{IN} = - V_{DDIOx}$	25	40	55	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Data based on design simulation only. Not tested in production.
2. The leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to *Table 45: I/O current injection susceptibility*.
3. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

All I/Os are CMOS- and TTL-compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 20* for standard I/Os, and in *Figure 21* for 5 V-tolerant I/Os. The following curves are design simulation results, not tested in production.

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to +/-8 mA, and sink or source up to +/- 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on V_{DDIOx}, plus the maximum consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 15: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on V_{SS}, plus the maximum consumption of the MCU sunk on V_{SS}, cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 15: Voltage characteristics*).

Output voltage levels

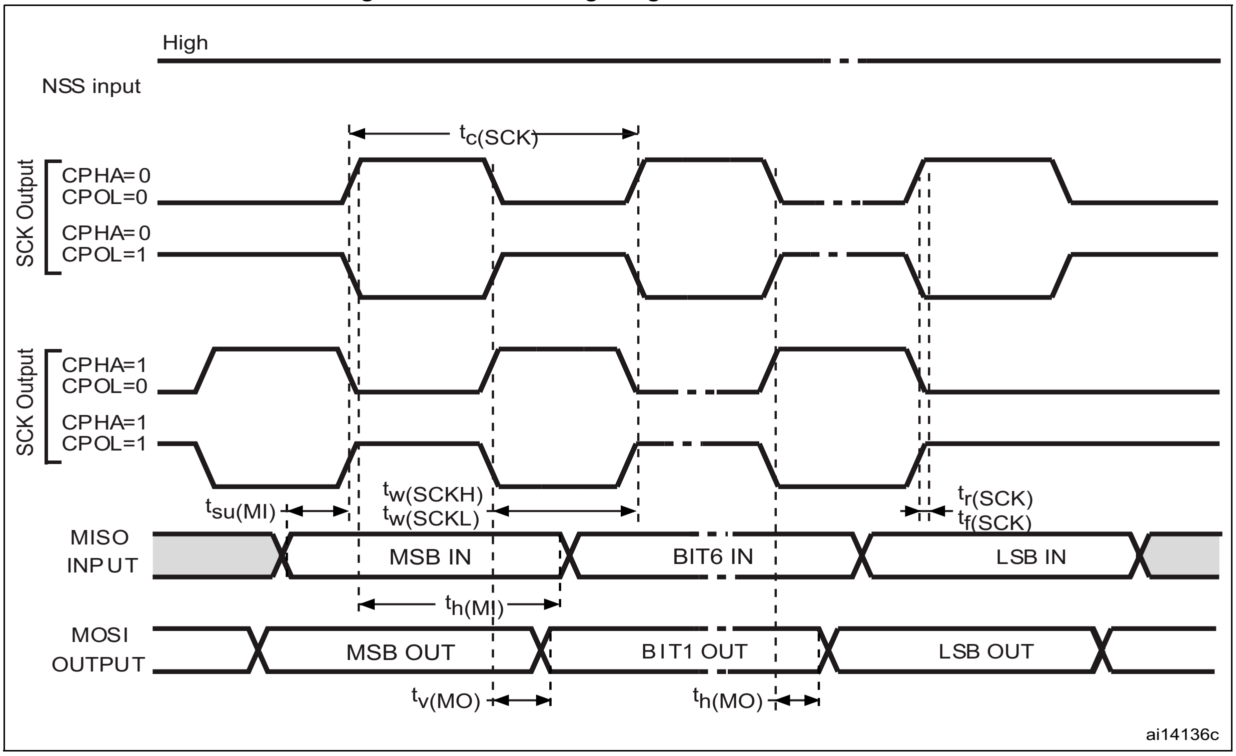
Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 18: General operating conditions*. All I/Os are CMOS- and TTL-compliant (FT, TTa or TC unless otherwise specified).

Table 47. Output voltage characteristics[1]

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level voltage for an I/O pin	CMOS port[2] $\|I_{IO}\|$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		$V_{DDIOx}-0.4$	-	
V_{OL}	Output low level voltage for an I/O pin	TTL port[2] $\|I_{IO}\|$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		2.4	-	
V_{OL}[3]	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	1.3	V
V_{OH}[3]	Output high level voltage for an I/O pin		$V_{DDIOx}-1.3$	-	
V_{OL}[3]	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 6 mA	-	0.4	V
V_{OH}[3]	Output high level voltage for an I/O pin		$V_{DDIOx}-0.4$	-	
V_{OLFm+}[3]	Output low level voltage for an FTf I/O pin in Fm+ mode	$\|I_{IO}\|$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
		$\|I_{IO}\|$ = 10 mA	-	0.4	V

1. The I_{IO} current sourced or sunk by the device must always respect the absolute maximum rating specified in *Table 15: Voltage characteristics*, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI_{IO}.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. Data based on characterization results. Not tested in production.

Figure 28. SPI timing diagram - master mode



1. Measurement points are done at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD}.

Table 60. I²S characteristics[(1)]

Symbol	Parameter	Conditions	Min	Max	Unit
f_{CK} $1/t_{c(CK)}$	I²S clock frequency	Master mode (data: 16 bits, Audio frequency = 48 kHz)	1.597	1.601	MHz
		Slave mode	0	6.5	
$t_{r(CK)}$	I²S clock rise time	Capacitive load C_L = 15 pF	-	10	ns
$t_{f(CK)}$	I²S clock fall time		-	12	
$t_{w(CKH)}$	I²S clock high time	Master f_{PCLK}= 16 MHz, audio frequency = 48 kHz	306	-	
$t_{w(CKL)}$	I²S clock low time		312	-	
$t_{v(WS)}$	WS valid time	Master mode	2	-	
$t_{h(WS)}$	WS hold time	Master mode	2	-	
$t_{su(WS)}$	WS setup time	Slave mode	7	-	
$t_{h(WS)}$	WS hold time	Slave mode	0	-	
DuCy(SCK)	I²S slave input clock duty cycle	Slave mode	25	75	%

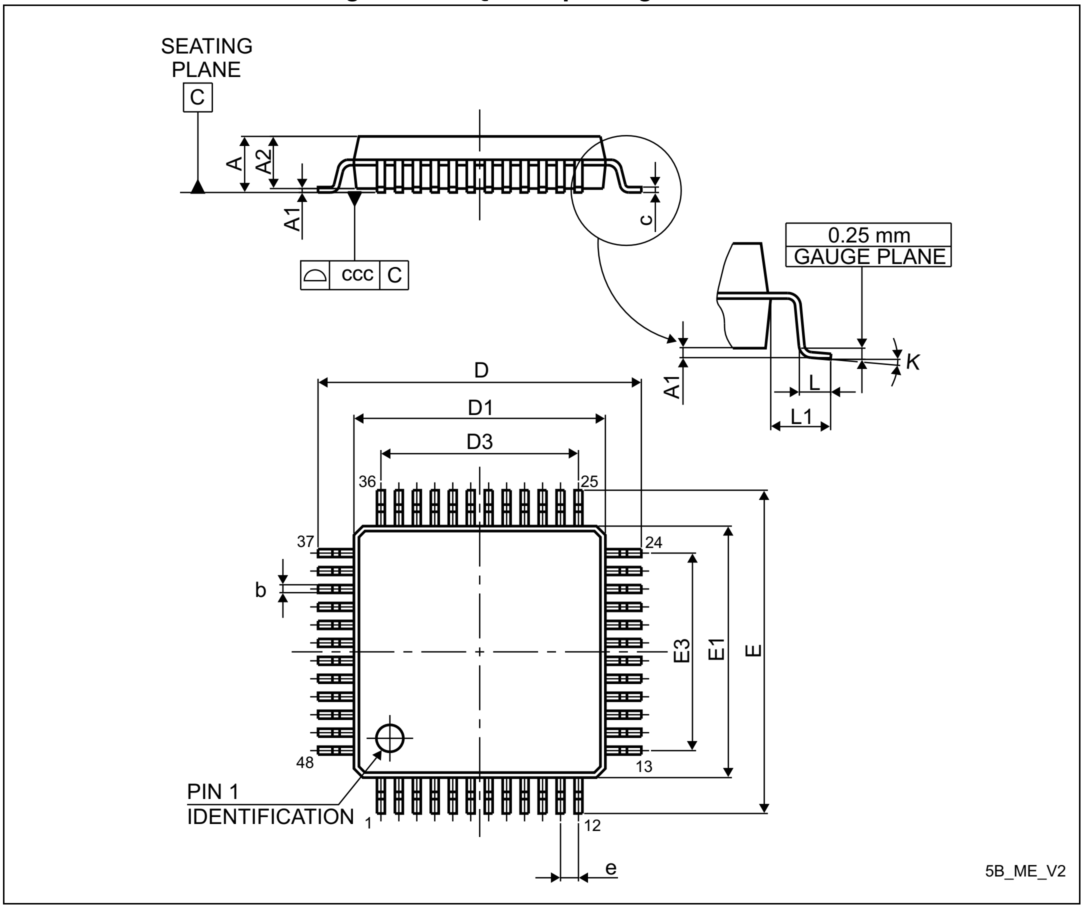
7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

7.1 LQFP48 package information

LQFP48 is a 48-pin, 7 x 7 mm low-profile quad flat package.

Figure 31. LQFP48 package outline

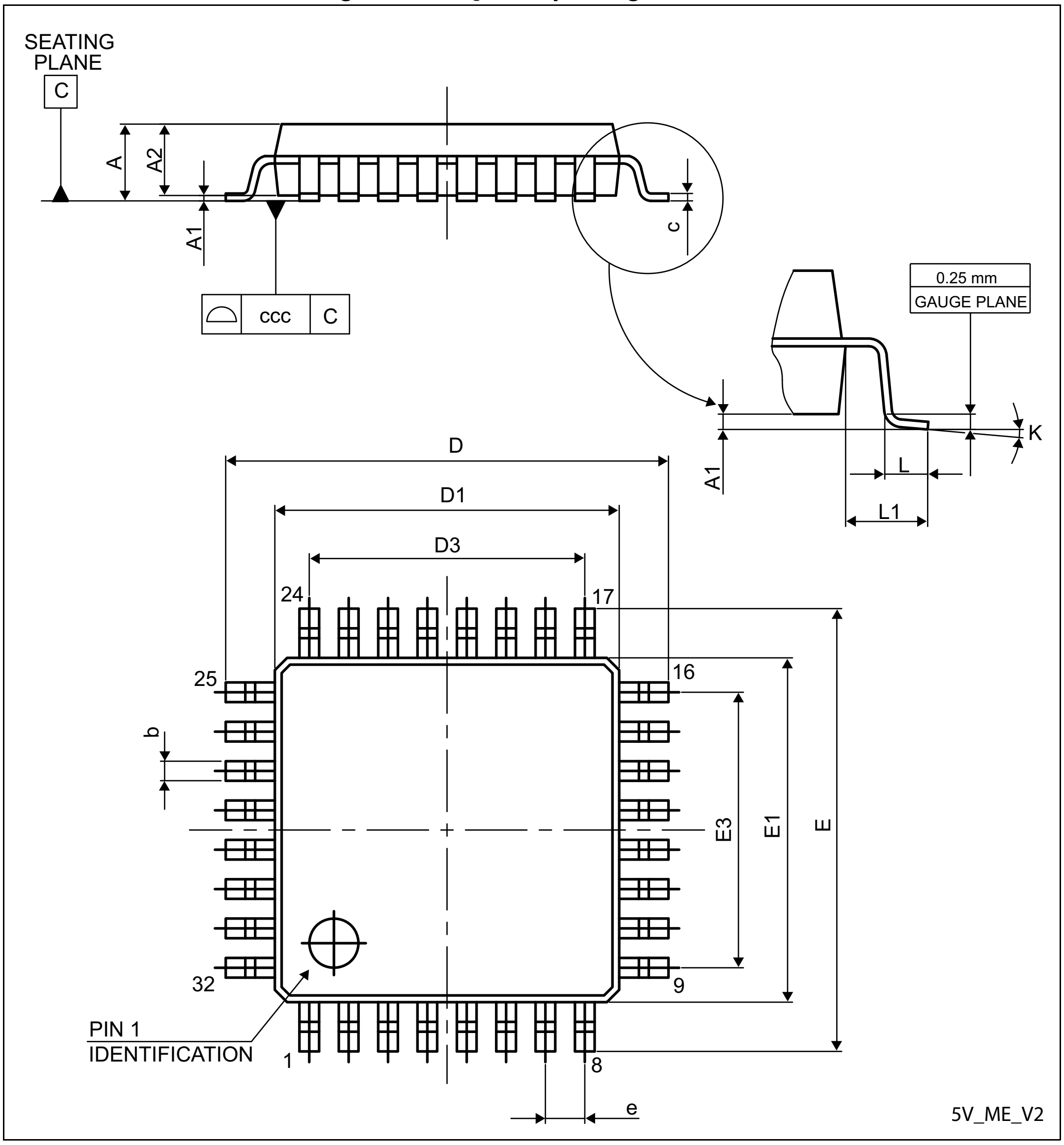


1. Drawing is not to scale.

7.2 LQFP32 package information

LQFP32 is a 32-pin, 7 x 7 mm low-profile quad flat package.

Figure 34. LQFP32 package outline



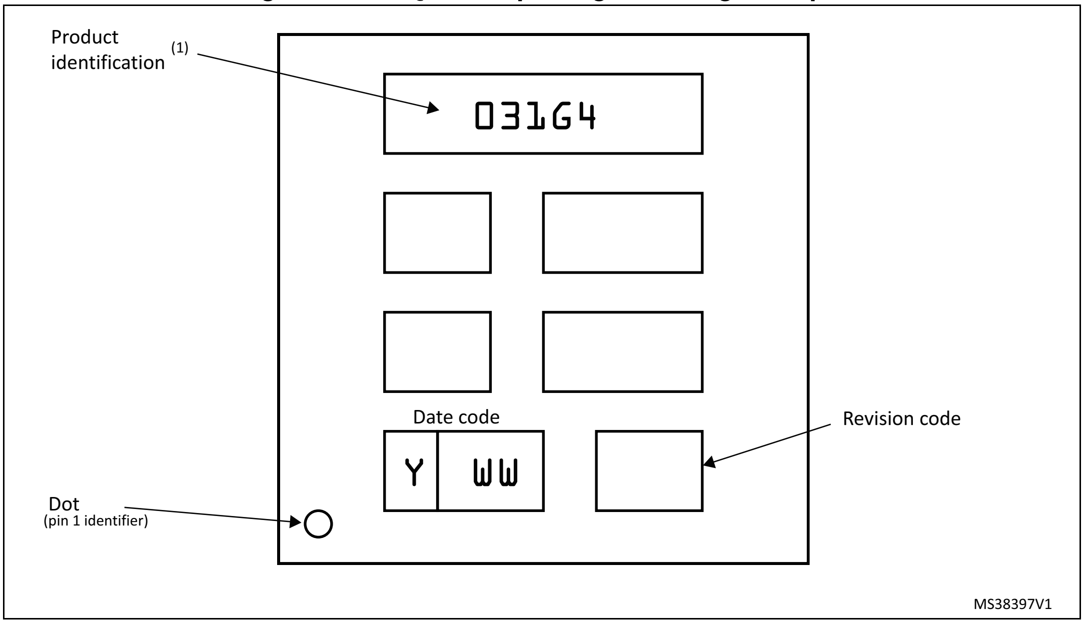
1. Drawing is not to scale.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 42. UFQFPN28 package marking example

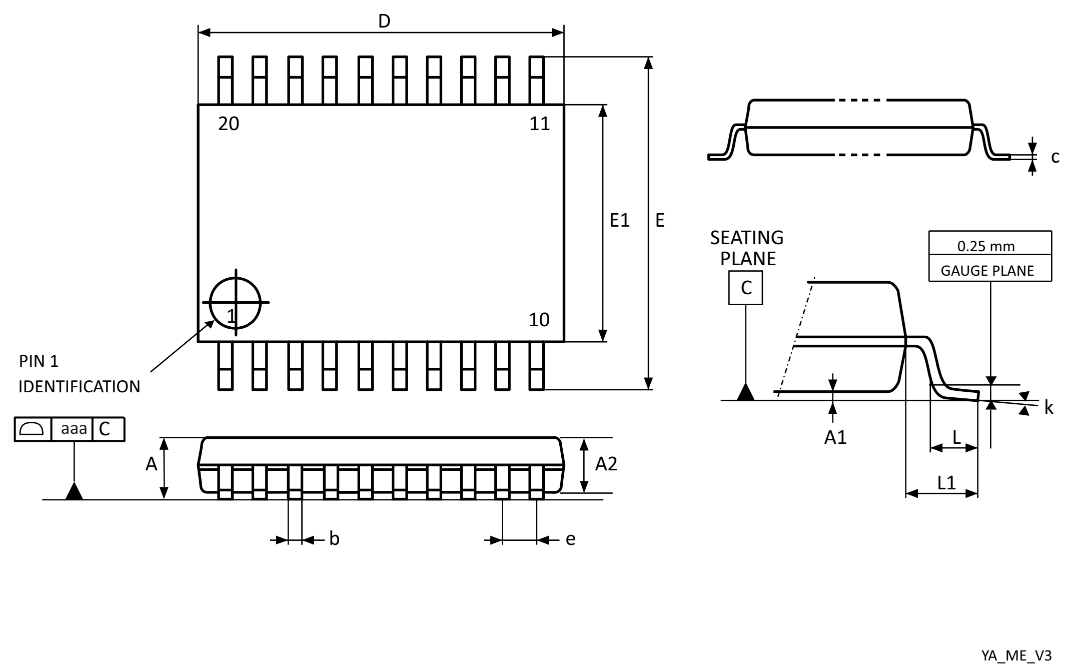


1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

7.6 TSSOP20 package information

TSSOP20 is a 20-lead thin shrink small-outline, 6.5 x 4.4 mm, 0.65 mm pitch, package.

Figure 46.TSSOP20 package outline



1. Drawing is not to scale.

Table 67. TSSOP20 package mechanical data

Symbol	millimeters			inches[(1)]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	-	1.200	-	-	0.0472
A1	0.050	-	0.150	0.0020	-	0.0059
A2	0.800	1.000	1.050	0.0315	0.0394	0.0413
b	0.190	-	0.300	0.0075	-	0.0118
c	0.090	-	0.200	0.0035	-	0.0079
D[(2)]	6.400	6.500	6.600	0.2520	0.2559	0.2598
E	6.200	6.400	6.600	0.2441	0.2520	0.2598
E1[(3)]	4.300	4.400	4.500	0.1693	0.1732	0.1772
e	-	0.650	-	-	0.0256	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-

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